

Round Type Infrared LED

Features:

- * Extra High Radiant Power and Radiant Intensity
- * Low Forward Voltage
- * Suitable for High Pulse Current Operation

Chip Materials:

- * Dice Material : GaAlAs/GaAs
- * Lens Color : Water Clear

Absolute Maximum Rating : (Ta = 25°C)

Symbol	Parameter	Max.	Unit
PD	Power Dissipation	200	mW
VR	Reverse Voltage	5	V
IF	Forward Current	100	mA
IPF	Peak forward current (F=1KHZ,duty=0.1)	800	mA
Topt	Operating Temperature Range	-35°C to 85°C	
Tstg	Storage Temperature Range	-35°C to 85°C	
Lead Soldering Temperature { 1.6mm(0.063 inch) From Body } 250°C ± 5°C for 3 Seconds			

Electro-Optical Characteristics : (Ta = 25°C)

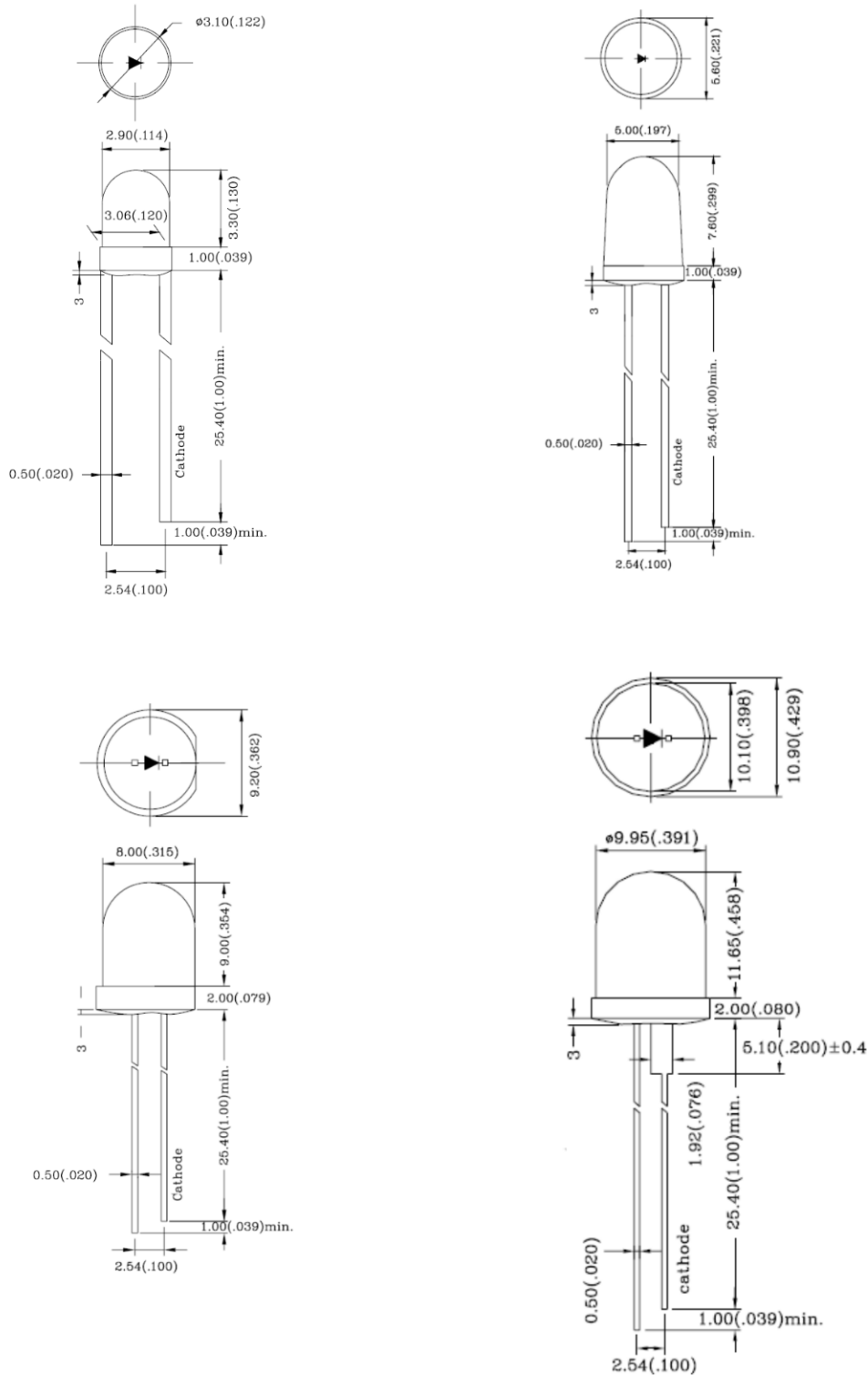
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
VF	Forward Voltage	IF = 20mA IF = 100mA		1.6 1.7	1.9 2.0	V
VFP	Peak Forward Voltage	IPF=800mA		2.2	2.5	V
IR	Reverse Current	VR = 5V			10	μA
λp	Peak Emission Wavelength	IF = 20mA		850		nm
2θ1/2	Half Intensity Angle	IF = 20mA		note2		deg
IE	Radiant Intensity	IF = 20mA IF=100mA	40	45 200		mw/sr

Note2 : Available 10,20,30,40,50,60,80,90 deg.

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Available: Dia. 3mm 5mm 8mm 10mm

Package Dimensions



Note:

1. All Dimensions are in millimeters.
2. Tolerance is $\pm 0.25\text{mm} (0.010 \text{ "})$
3. Protruded resin under flange is $1.5\text{mm} (0.059 \text{ "})$ max.